L Number		Search Text	DB	Time stamp
1	2	438/197.ccls. and "stack structure" and	USPAT	2003/07/24 11:58
•		photoresist and teos		
-	387		USPAT	2003/07/16 11:50
-		438/197.ccls. and substrate	USPAT	2003/07/16 11:58
-	89	438/197.ccls. and substrate and "conductive	USPAT	2003/07/16 11:51
		layer"		
_	39	438/197.ccls. and substrate and "conductive	USPAT	2003/07/16 11:51
		layer" and "dielectric layer"		
_	0		USPAT	2003/07/16 11:51
	Ū	layer" and "dielectric layer" and "buried		,
		drain"		
	2.7		USPAT	2003/07/16 11:52
-		438/197.ccls. and substrate and "conductive	USPAI	2003/07/10 11:32
		layer" and "dielectric layer" and "drain"		2002/07/16 11 52
-	10	438/197.ccls. and substrate and "conductive	USPAT	2003/07/16 11:52
		layer" and "dielectric layer" and "drain"		
		and "insulating layer"		
- 1	3	438/197.ccls. and substrate and "conductive"	USPAT	2003/07/16 11:53
		layer" and "dielectric layer" and "drain"		
		and "insulating layer" and "silicon layer"		
-	0	438/197.ccls. and substrate and "conductive	USPAT	2003/07/16 11:53
	3	layer" and "dielectric layer" and "drain"		
		and "insulating layer" and "silicon layer"	1	
1	_	and cap	USPAT	2003/07/16 11:53
-	2	438/197.ccls. and substrate and "conductive	USPAI	2003/07/16 11:53
		layer" and "dielectric layer" and "drain"		
		and "insulating layer" and "silicon layer"	:	i
		and nitride	I	
- ;	2	438/197.ccls. and substrate and "conductive	USPAT	2003/07/16 11:53
		layer" and "dielectric layer" and "drain"		
		and "insulating layer" and "silicon layer"		
:		and nitride and gate		İ
_	6	438/197.ccls. and "non volatile memory"	USPAT	2003/07/16 11:59
- I	0	438/197.ccls. and "non volatile memory" and	USPAT	2003/07/16 11:59
-	б	substrate		
1	_		USPAT	2003/07/16 12:05
-	6	438/197.ccls. and "non volatile memory" and	USFAI	2003/07/10 12.03
!		substrate and conductive	TIONAM	2002/07/16 12:00
-	2	438/197.ccls. and "non volatile memory" and	USPAT	2003/07/16 12:09
		substrate and conductive and dielectric		0000/07/77 70 77
- :		438/197.ccls. and "strip stack"	USPAT	2003/07/16 12:09
-		438/197.ccls. and "stack"	USPAT	2003/07/16 12:09
-	6	438/197.ccls. and "stack structure"	USPAT	2003/07/17 10:42
-	6	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:10
i	,	semiconductor	İ	į
-	6		USPAT	2003/07/16 12:10
	3	substrate		
	_	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:10
-	6		COLLI	i
		substrate and gate	· IICDAT	2003/07/16 12:10
-	4	438/197.ccls. and "stack structure" and	USPAT	2003/07/10 12:10
		substrate and gate and dielectric	110022	2002/07/16 10 11
-	0	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:11
į		substrate and gate and dielectric and buri\$4		1
-	4	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:11
		substrate and gate and dielectric and drain		
_	4	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:11
	•	substrate and gate and dielectric and drain		
		and insulat\$4		
	.4	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:11
-	4	substrate and gate and dielectric and drain		,,
			1	!
,	_	and insulat\$4 and silicon	HCDAM	2003/07/16 12:12
-	2	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:12
		substrate and gate and dielectric and drain		
		and insulat\$4 and silicon and cap		2005/55/55
→	1	438/197.ccls. and "stack structure" and	USPAT	2003/07/16 12:12
		substrate and gate and dielectric and drain		
		and insulat\$4 and silicon and cap and line\$4		
_	1		USPAT	2003/07/16 12:13
	<u> </u>	substrate and gate and dielectric and drain	-	•
		and insulat\$4 and silicon and cap and line\$4		
		and salicide		

-	i	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4	USPAT	2003/07/17 10:42
•		and insurated and silicon and cap and linesd and salicide and metal		
-	4	438/197.ccls. and "stack structure" and photoresist	USPAT	2003/07/24 11:58
-	1	substrate and gate and dielectric and drain	USPAT	2003/07/17 10:43
		and insulat\$4 and silicon and cap and line\$4 and salicide and metal and photoresist		· 1